

**AMENDMENTS TO THE CLAIMS:**

This listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently Amended) An inspection probe for inspecting electrical properties of a semiconductor device, comprising:
  - a base member;
  - wiring layers mounted on an outer surface of the base member;
  - probe pins having tips, the probe pins electrically connected to and contacting the wiring layers, the probe pins further protruding from the base member;
  - first metal layers provided to the tips of the probe pins; and
  - second metal layers formed on the wiring layers, the second metal layers being made of a material different from that of the probe pins,
    - wherein the first metal layers and the second metal layers are physically separated from each other by the probe pins.
2. (Original) The inspection probe according to Claim 1, wherein the first metal layers are made of a material having good contact properties selected depending on a material of external terminal electrodes of the semiconductor device.
3. (Original) The inspection probe according to Claim 1, wherein the second metal layers have a volume resistivity less than that of the wiring layers.
4. (Original) The inspection probe according to Claim 1, wherein the base member has a plurality

of the probe pins.

5. (Previously Presented) The inspection probe according to Claim 1, wherein the first metal layers and the second metal layers are made of the homogeneous material.

6. (Previously Presented) The inspection probe according to Claim 1, wherein the first metal layers and the second metal layers are made of heterogeneous material.

7. (Previously Presented) The inspection probe according to Claim 1, wherein the first metal layers have hardness higher than that of the external terminal electrodes of the semiconductor device.

8. (Previously Presented) The inspection probe according to Claim 1, wherein a region for forming each first metal layer has a width wider than or equal to half of the width of the probe pins and a length longer than or equal to the sum of 1.0 time the size of the electrodes, the distance that the inspection probe is moved after the inspection probe coming in contact with the electrodes, the longitudinal positional tolerance of the probe pins, and the length determined based on the positional tolerance of the electrodes.

9. (Previously Presented) The inspection probe according to Claim 1, wherein the probe pins form an angle of 0 to 45 degrees with respect to a face on which the electrodes of the semiconductor device are formed.

10. (Previously Presented) The inspection probe according to Claim 1, further comprising a flexible, electrically connectable wiring substrate placed between the base member and a inspection substrate and a backup plate mounted on the inspection substrate, for mounting the base member thereon if the electrodes of the semiconductor device are arranged at sides thereof, correspond to multiple pins, and must be connected to the inspection substrate.

11. (Currently Amended) [[The]] An inspection probe for inspecting electrical properties of a semiconductor device, according to Claim 10, further comprising:

a base member;

wiring layers mounted on the base member;

probe pins having tips, electrically connected to the wiring layers, protruding from the base member;

first metal layers provided to the tips of the probe pins;

second metal layers formed on the wiring layers, the second metal layers being made of a material different from that of the probe pins, the second metal layers physically separated from the first metal layers by the probe pins;

a flexible, electrically connectable wiring substrate placed between the base member and a inspection substrate and a backup plate mounted on the inspection substrate, for mounting the base member thereon if the electrodes of the semiconductor device are arranged at sides thereof, correspond to multiple pins, and must be connected to the inspection substrate; and

a support substrate which is integrated with peripheral portions of the base member with an adhesive member placed therebetween and which is made of the same material as a material of the base member, said support substrate being mounted on the inspection substrate, wherein the

backup plate has a protrusive portion at a center area thereof such that the probe pins form a predetermined angle with respect to the electrodes of the semiconductor device.

12. (Previously Presented) The inspection probe according to Claim 11, wherein the backup plate and the inspection substrate each has a perforations partly.

13. (Previously Presented) The inspection probe according to Claim 11, wherein the base member has warpage-reducing means for reducing the warpage thereof.

14. (Previously Presented) The inspection probe according to Claim 13, wherein the warpage-reducing means include a warpage-correcting plate attached to the rear face of the base member.

15. (Previously Presented) The inspection probe according to Claim 13, wherein the warpage-reducing means include notches formed at end faces of the base member.

16. (Previously Presented) The inspection probe according to Claim 13, wherein the warpage-reducing means include notches formed at edges of the base member at which bending occurs.

17. (Previously Presented) The inspection probe according to Claim 13, wherein the warpage-reducing means include a plurality of notches, formed in the rear face of the base member, having a depth insufficient to cause negative effects on the main surface of the base member and

wires.

18. (Previously Presented) The inspection probe according to Claim 17, wherein the plurality of notches extend laterally.

19. (Previously Presented) The inspection probe according to Claim 17, wherein the plurality of notches extend longitudinally.

20. (Previously Presented) The inspection probe according to Claim 17, wherein the plurality of notches extend laterally and longitudinally.